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Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS					
I _{T(AV)} 35 A					
V _{DRM} /V _{RRM}	800 V, 1200 V				
V _{TM}	1.45 V				
I _{GT}	150 mA				
T _J	-40 °C to +125 °C				
Package	TO-247AC 3L				
Circuit configuration	Single SCR				

FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- Low IGT parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

DESCRIPTION

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	35	Δ.		
I _{RMS}		55	- A		
V _{RRM} /V _{DRM}		800 to 1200	V		
I _{TSM}		600	А		
V _T	40 A, T _J = 25 °C	1.45	V		
dV/dt		1000	V/µs		
dl/dt		100	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-40TPS08A-M3	800	900				
VS-40TPS08-M3	800	900	10			
VS-40TPS12A-M3	1200	1300	10			
VS-40TPS12-M3	1200	1300				



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 79 °C, 180° conduction half sine wav	е	35	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			55	Α
Maximum peak, one-cycle	L	10 ms sine pulse, rated V _{RRM} applied		500	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied		600	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied	Initial $T_{.1} = T_{.1} max$.	1250	A ² s
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	ij – ijiilax.	1760	A ² S
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied	t = 0.1 ms to 10 ms, no voltage reapplied		A ² √s
Low level value of threshold voltage	V _{T(TO)1}	·		1.02	V
High level value of threshold voltage	V _{T(TO)2}	T 105 00	1.23	V	
Low level value of on-state slope resistance	r _{t1}	T _J = 125 °C		9.74	0
High level value of on-state slope resistance	r _{t2}			7.50	mΩ
Maximum peak on-state voltage	V_{TM}	110 A, T _J = 25 °C		1.85	V
Maximum rate of rise of turned-on current	dl/dt	T _J = 25 °C		100	A/µs
Maximum holding current	I _H	Anode supply = 6 V, resistive load, initial T	= 1 A, I _T = 25 °C	200	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		300	
		$T_{J} = 25 ^{\circ}\text{C}$ $T_{J} = 125 ^{\circ}\text{C}$ $V_{R} = \text{Rated V}_{RRM} / V_{DRM}$		0.5	mA
Maximum reverse and direct leakage current	I _{RRM/} I _{DRM}			10	
Maximum rate of rise of off-state voltage 40TPS12A	a) (/d+	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R_g - k = 100 Ω		500	\//··-
Maximum rate of rise of off-state voltage 40TPS12	dV/dt			1000	V/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			10	W
Maximum average gate power	P _{G(AV)}			2.5	VV
Maximum peak gate current	I _{GM}			2.5	Α
Maximum peak negative gate voltage	- V _{GM}			10	V
		T _J = - 40 °C		4.0	
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	2.5	V
		T _J = 125 °C	- resistive lead	1.7	
	I _{GT}	T _J = - 40 °C	Anode supply = 6 V resistive load	270	mA
Maximum vaguired DC gate august to triager		T _J = 25 °C		150	
Maximum required DC gate current to trigger		T _J = 125 °C		80	
		T_J = 25 °C, for 40TPSAPbF and 40TPSA-M3		40	
Maximum DC gate voltage not to trigger for 40TPS12	V_{GD}	T _J = 125 °C, V _{DRM} = rated value		0.25	V
Maximum DC gate current not to trigger for 40TPS12	I _{GD}			6	mA
Maximum DC gate voltage not to trigger for 40TPS12A	V_{GD}	T _J = 125 °C, V _{DRM} = rated value		0.15	V
Maximum DC gate current not to trigger for 40TPS12A	I _{GD}			1	mA

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.6		
Maximum thermal resistance, junction to ambient	R _{thJA}	DC operation	40	°C/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.2		
Approximate weight			6	g	
Approximate weight			0.21	oz.	
Mounting torque minimum			6 (5)	kgf · cm	
Mounting torque maximum			12 (10)	(lbf \cdot in)	
			40TPS08A		
Marking dovice		Case style TO-247AC 3L	40TPS12A		
Marking device			40TPS08		
			40TF	PS12	

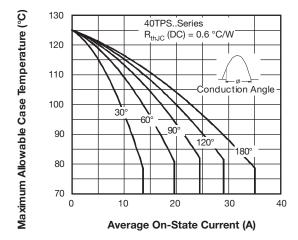


Fig. 1 - Current Rating Characteristics

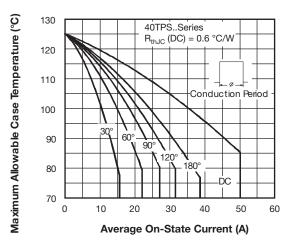


Fig. 2 - Current Rating Characteristics

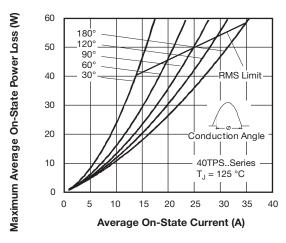


Fig. 3 - On-State Power Loss Characteristics

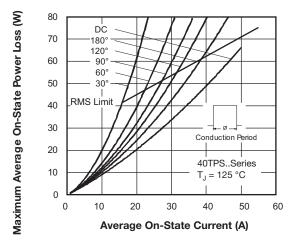


Fig. 4 - On-State Power Loss Characteristics



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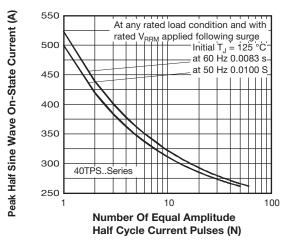


Fig. 5 - Maximum Non-Repetitive Surge Current

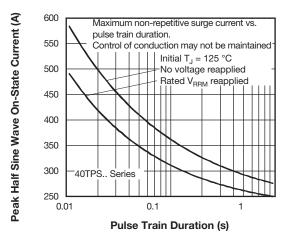


Fig. 6 - Maximum Non-Repetitive Surge Current

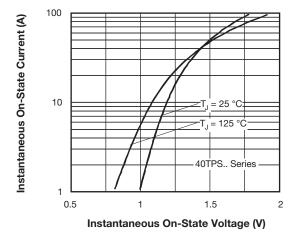


Fig. 7 - On-State Voltage Drop Characteristics



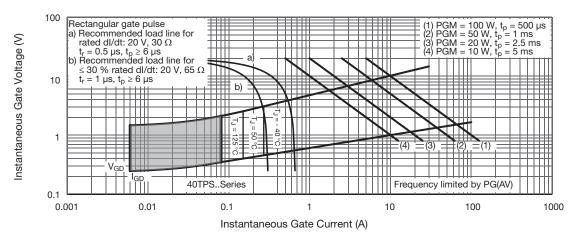


Fig. 8 - Gate Characteristics

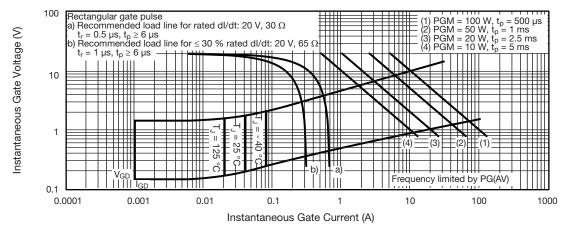


Fig. 9 - Gate Characteristics, 40TPS..A Series

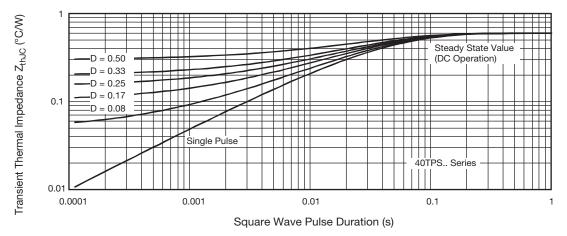
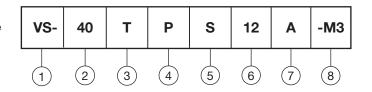


Fig. 10 - Thermal Impedance ZthJC Characteristics

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (40 = 40 A)

3 - Circuit configuration:

T = thyristor

4 - Package:

P = TO-247AC 3L

5 - Type of silicon:

S = standard recovery rectifier

V = 800

Voltage ratings

12 = 1200 V

- • A = low I_{GT} selection 40 mA maximum

• None = standard lgt selection

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-40TPS08A-M3	25	500	Antistatic plastic tubes		
VS-40TPS08-M3	25	500	Antistatic plastic tubes		
VS-40TPS12A-M3	25	500	Antistatic plastic tubes		
VS-40TPS12-M3	25	500	Antistatic plastic tubes		

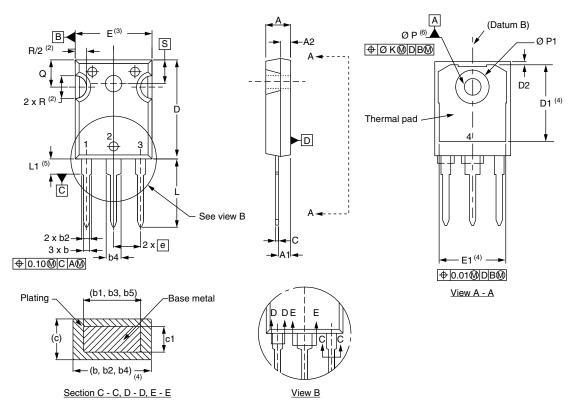
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96138</u>				
Part marking information	www.vishay.com/doc?95007			



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TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
OTIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.2	0.254)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217	BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension Q



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